



H06N60 Series

N-Channel Power Field Effect Transistor

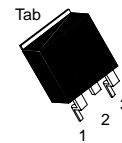
Description

This high voltage MOSFET uses an advanced termination scheme to provide enhanced voltage-blocking capability without degrading performance over time. In addition, this advanced MOSFET is designed to withstand high energy in avalanche and commutation modes. The new energy efficient design also offers a drain-to-source diode with a fast recovery time. Designed for high voltage, high speed switching applications in power supplies, converters and PWM motor controls, these devices are particularly well suited for bridge circuits where diode speed and commutating safe operating areas are critical and offer additional and safety margin against unexpected voltage transients.

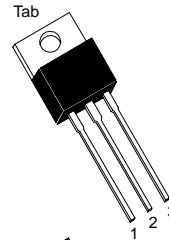
Features

- Robust High Voltage Termination
- Avalanche Energy Specified
- Source-to-Drain Diode Recovery Time Comparable to a Discrete Fast Recovery Diode
- Diode is Characterized for Use in Bridge Circuits
- IDSS and $V_{DS(on)}$ Specified at Elevated Temperature

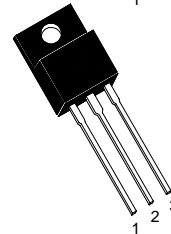
H06N60 Series Pin Assignment



3-Lead Plastic **TO-263**
 Package Code: U
 Pin 1: Gate
 Pin 2 & Tab: Drain
 Pin 3: Source

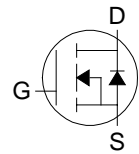


3-Lead Plastic **TO-220AB**
 Package Code: E
 Pin 1: Gate
 Pin 2 & Tab: Drain
 Pin 3: Source



3-Lead Plastic **TO-220FP**
 Package Code: F
 Pin 1: Gate
 Pin 2: Drain
 Pin 3: Source

H06N60 Series
 Symbol:



Absolute Maximum Ratings

Symbol	Parameter	Value	Units
I_D	Drain to Current (Continuous)	6	A
I_{DM}	Drain to Current (Pulsed)	24	A
V_{GS}	Gate-to-Source Voltage (Continue)	± 30	V
P_D	Total Power Dissipation ($T_C=25^\circ\text{C}$) H06N60U (TO-263)	110	W
	H06N60E (TO-220AB)	110	W
	H06N60F (TO-220FP)	40	W
P_D	Derate above 25°C H06N60U (TO-263)	0.58	W/ $^\circ\text{C}$
	H06N60E (TO-220AB)	0.58	W/ $^\circ\text{C}$
	H06N60F (TO-220FP)	0.33	W/ $^\circ\text{C}$
T_j	Operating Temperature Range	-55 to 150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
E_{AS}	Single Pulse Drain-to-Source Avalanche Enrgy- $T_j=25^\circ\text{C}$ ($V_{DD}=100\text{V}$, $V_{GS}=10\text{V}$, $I_L=6\text{A}$, $L=10\text{mH}$, $R_G=25\Omega$)	250	mJ
T_L	Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	260	$^\circ\text{C}$

Note: 1. $V_{DD}=50\text{V}$, $I_D=10\text{A}$
 2. Pulse Width and frequency is limited by $T_{j(max)}$ and thermal response



Thermal Characteristics

Symbol	Parameter	Value		Units
$R\theta_{JC}$	Thermal Resistance Junction to Case Max.	TO-263	1.7	$^{\circ}\text{C/W}$
		TO-220AB	1.7	
		TO-220FP	3.3	
$R\theta_{JA}$	Thermal Resistance Junction to Ambient Max.	62		$^{\circ}\text{C/W}$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage ($V_{GS}=0V, I_D=250\mu\text{A}$)	600	-	-	V
I_{DSS}	Drain-Source Leakage Current ($V_{DS}=600V, V_{GS}=0V$)	-	-	1	μA
	Drain-Source Leakage Current ($V_{DS}=600V, V_{GS}=0V, T_J=125^{\circ}\text{C}$)	-	-	50	μA
I_{GSSF}	Gate-Source Leakage Current-Forward ($V_{gsf}=30V, V_{DS}=0V$)	-	-	100	nA
I_{GSSR}	Gate-Source Leakage Current-Reverse ($V_{gsr}=-30V, V_{DS}=0V$)	-	-	-100	nA
$V_{GS(th)}$	Gate Threshold Voltage ($V_{DS}=V_{GS}, I_D=250\mu\text{A}$)	2	3	4	V
$R_{DS(on)}$	Static Drain-Source On-Resistance ($V_{GS}=10V, I_D=3.6A$)*	-	1	1.2	Ω
g_{FS}	Forward Transconductance ($V_{DS}=15V, I_D=3.6A$)*	2	4	-	S
C_{iss}	Input Capacitance	-	1100	-	pF
C_{oss}	Output Capacitance	-	150	-	
C_{riss}	Reverse Transfer Capacitance	-	25	-	
$t_{d(on)}$	Turn-on Delay Time	-	14	-	ns
t_r	Rise Time	-	19	-	
$t_{d(off)}$	Turn-off Delay Time	-	40	-	
t_f	Fall Time	-	26	-	
Q_g	Total Gate Charge	-	35.5	50	nC
Q_{gs}	Gate-Source Charge	-	8.1	-	
Q_{gd}	Gate-Drain Charge	-	14.1	-	
L_D	Internal Drain Inductance (Measured from the drain lead 0.25" from package to center of die)	-	4.5	-	nH
L_S	Internal Drain Inductance (Measured from the drain lead 0.25" from package to source bond pad)	-	7.5	-	nH

*: Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

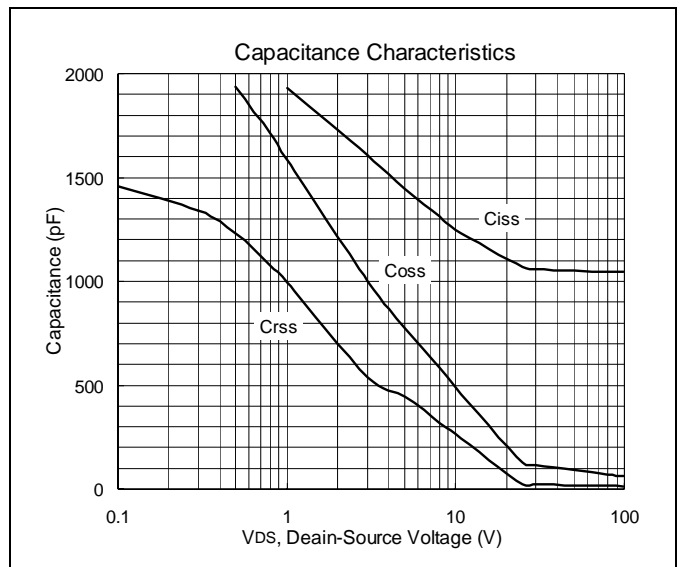
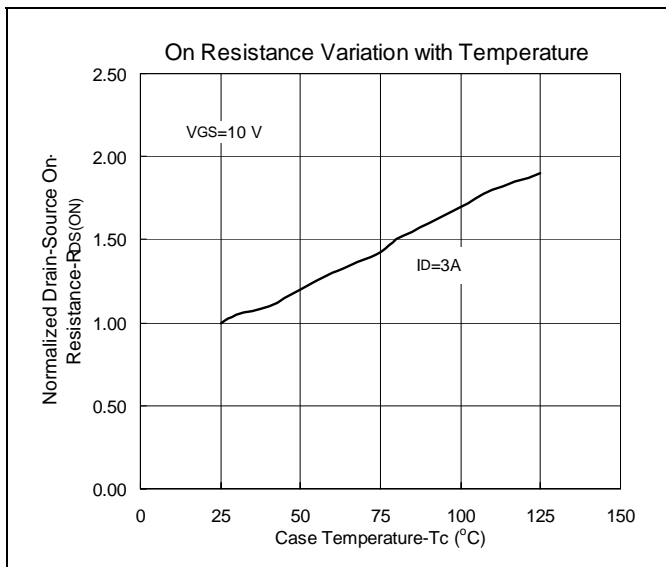
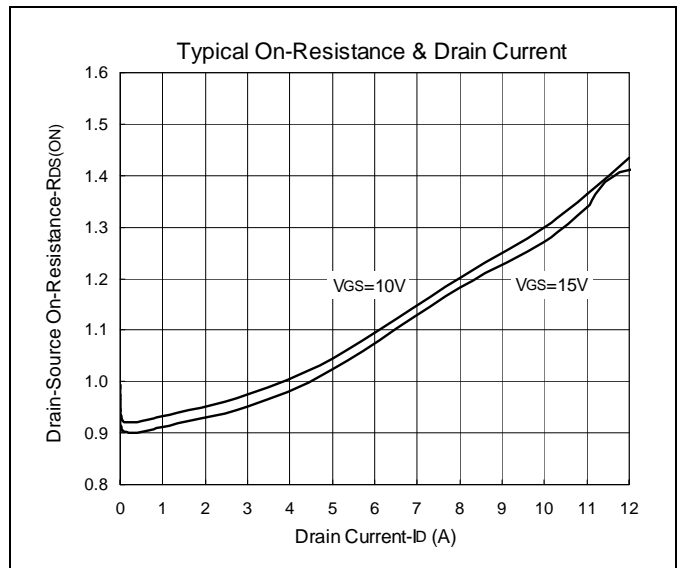
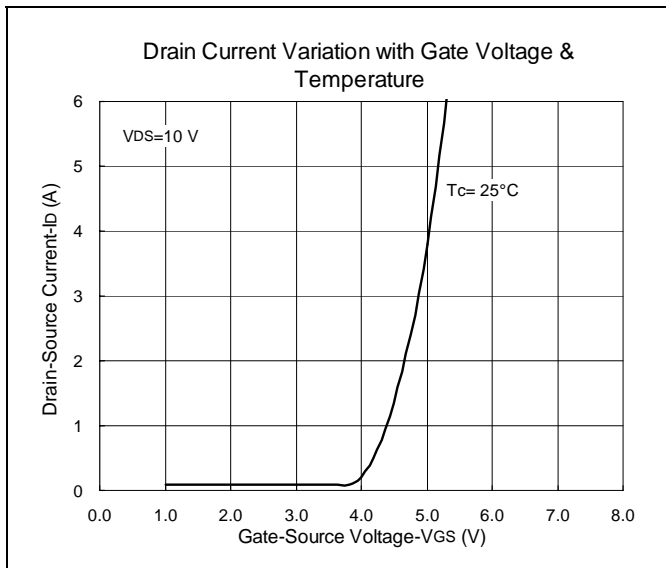
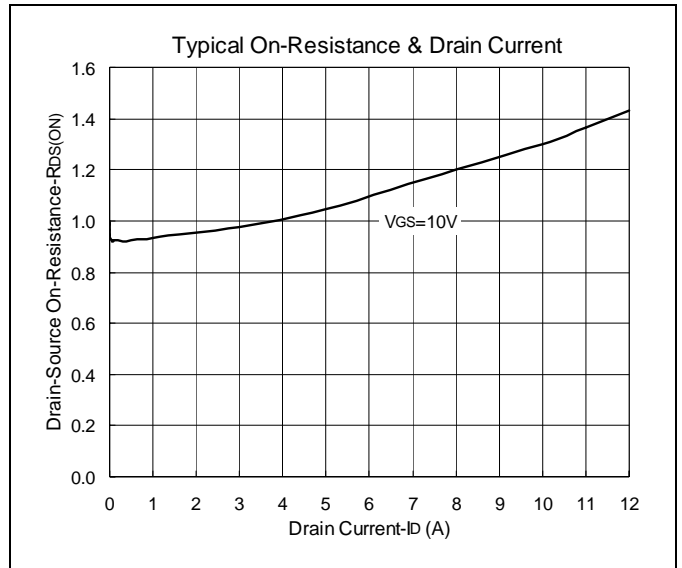
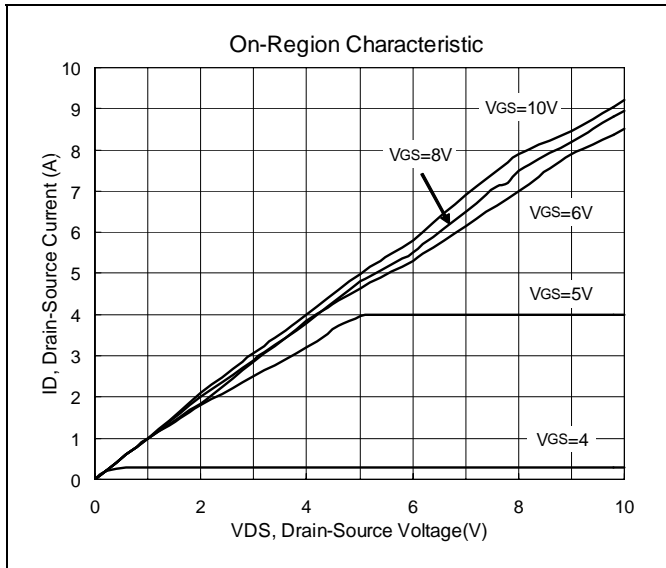
Source-Drain Diode

Symbol	Characteristic	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage(1)	-	-	1.2	V
t_{on}	Forward Turn-On Time	-	**	-	ns
t_{rr}	Reverse Recovery Time	-	266	-	ns

** : Negligible, Dominated by circuit inductance



Characteristics Curve





TO-220AB Dimension

3-Lead TO-220AB
 Plastic Package
 HSMC Package Code: E

Marking:

Pb Free Mark
 Pb-Free: "●" (Note)
 Normal: None

Date Code Control Code

Note: Green label is used for pb-free packing

Pin Style: 1.Gate 2 & Tab.Drain 3.Source

Material:

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	5.58	7.49
B	8.38	8.90
C	4.40	4.70
D	1.15	1.39
E	0.35	0.60
F	2.03	2.92
G	9.66	10.28
H	-	*16.25
I	-	*3.83
J	3.00	4.00
K	0.75	0.95
L	2.54	3.42
M	1.14	1.40
N	-	*2.54
O	12.70	14.27
P	14.48	15.87

*: Typical, Unit: mm

TO-220FP Dimension

3-Lead TO-220FP
 Plastic Package
 HSMC Package Code: F

Marking:

Pb Free Mark
 Pb-Free: "●" (Note)
 Normal: None

Date Code Control Code

Note: Green label is used for pb-free packing

Pin Style: 1.Gate 2.Drain 3.Source

Material:

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	6.48	7.40
C	4.40	4.90
D	2.34	3.00
E	0.45	0.80
F	9.80	10.36
G	3.10	3.60
I	2.70	3.43
J	0.60	1.00
K	2.34	2.74
L	12.48	13.60
M	15.67	16.20
N	0.90	1.47
O	2.00	2.96
$\alpha 1/2/4/5$	-	*5°
$\alpha 3$	-	*27°

*: Typical, Unit: mm



TO-263 Dimension

3-Lead TO-263 Plastic
Surface Mount Package
HSMC Package Code: U

(): Reference Dimension, Unit: mm

DIM	Min.	Max.	DIM	Max.	Max.	DIM	Min.	Max.
A	9.70	10.10	L	4.30	4.70	W	-	(7.20)
B	1.00	1.40	M	1.25	1.40	X	-	(0.40)
C	-	(4.60)	N	-0.05	0.25	Y	-	(0.90)
D	9.00	9.40	O	2.20	2.60	a1	-	(15°)
E	4.70	5.10	P	1.90	2.10	a2	-	(3°)
F	15.00	15.60	Q	-	(0.75)	a3	-	0°-3°
G	-	(0.40)	R	2.24	2.84	r1	-	(ϕ 1.50)
H	1.20	1.60	S	0.45	0.60	r2	-	0.30
I	1.17	1.37	T	9.80	10.20	r3	-	(0.45)
J	0.70	0.90	U	-	(7.00)	DP	-	(0.20)
K	2.34	2.74	V	-	(4.00)			

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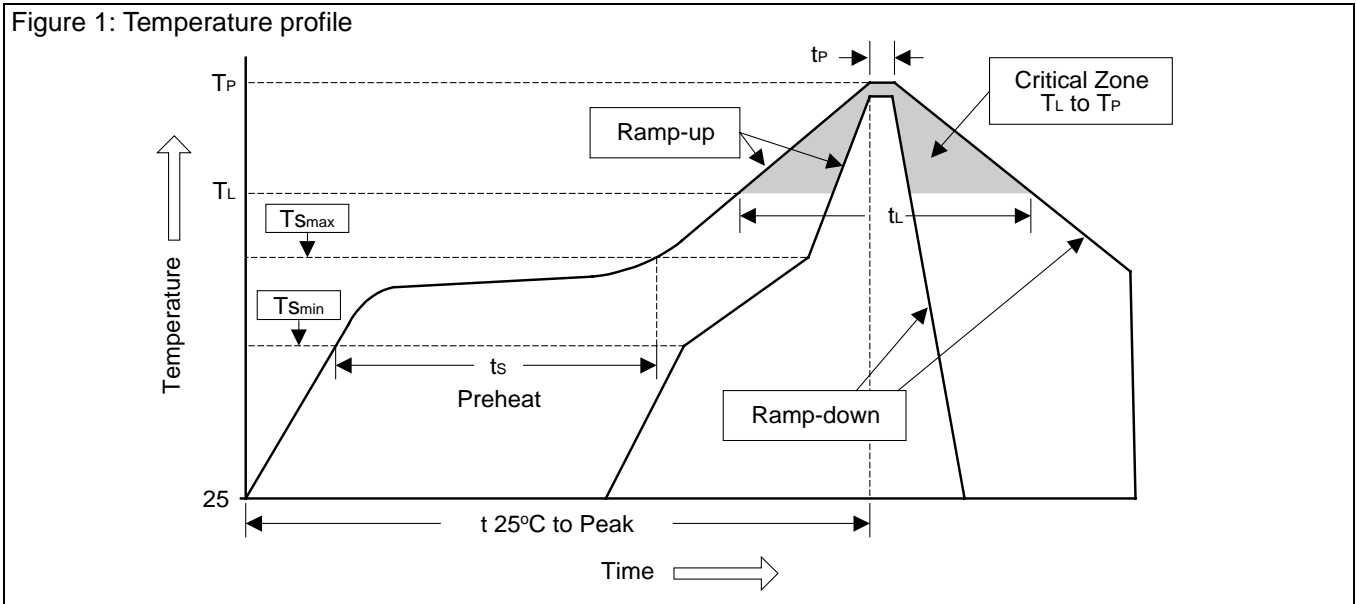
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Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	$<3^{\circ}\text{C}/\text{sec}$	$<3^{\circ}\text{C}/\text{sec}$
Preheat		
- Temperature Min (T_{Smin})	100°C	150°C
- Temperature Max (T_{Smax})	150°C	200°C
- Time (min to max) (t_s)	60~120 sec	60~180 sec
T_{Smax} to T_L		
- Ramp-up Rate	$<3^{\circ}\text{C}/\text{sec}$	$<3^{\circ}\text{C}/\text{sec}$
Time maintained above:		
- Temperature (T_L)	183°C	217°C
- Time (t_L)	60~150 sec	60~150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_P)	10~30 sec	20~40 sec
Ramp-down Rate	$<6^{\circ}\text{C}/\text{sec}$	$<6^{\circ}\text{C}/\text{sec}$
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec